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## ON Semiconductor®

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### FDBL0120N40

2014年11月

### N 沟道 PowerTrench<sup>®</sup> MOSFET 40 V, 240 A, 1.2 $m\Omega$

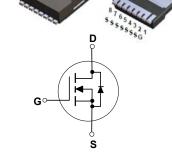
### 特性

- 典型值  $R_{DS(on)}$  = 0.9  $m\Omega$  ( $V_{GS}$  = 10 V,  $I_D$  = 80 A)
- 典型值  $Q_{g(tot)}$  = 90 nC ( $V_{GS}$  = 10 V,  $I_D$  = 80 A)
- UIS 能力
- 符合 RoHS 标准

### 应用

- 工业电机驱动器
- 工业电源
- 工业自动化
- 电动工具
- 电池保护
- 太阳能逆变器
- UPS 和能源逆变器
- 储能
- 负载开关





如需最新封装图纸,请访问 Fairchild 网站: https://www.fairchildsemi.com/evaluate/packagespecifications/packageDetails.html?id=PN\_PSOFA-008

### MOSFET 最大额定值 T<sub>J</sub> = 25 °C,除非另有说明。

符号	参数	额定值	单位		
$V_{DSS}$	漏极至源极电压的关系		40	V	
$V_{GS}$	栅极至源极电压		±20	V	
I_	漏极电流-连续(V <sub>GS</sub> =10)(注 1)	T <sub>C</sub> = 25 °C	240	Α	
ID	脉冲漏电流	T <sub>C</sub> = 25 °C	见图 4	^	
E <sub>AS</sub>	单脉冲雪崩能量	(注2)	316	mJ	
D_	功耗		300	W	
$P_{D}$	超过 25 °C 时降额		2.0	W/°C	
$T_J$ , $T_{STG}$	工作和存储温度		-55 至 + 175	°C	
$R_{\theta JC}$	结点一壳体的热阻		0.5	°C/W	
$R_{\thetaJA}$	结至环境热阻最大值	(注 3)	43	°C/W	

- 1: 电流受接合线配置限制。

### 封装标识与定购信息

器件标识	器件	封装			
FDBL0120N40	FDBL0120N40	MO-299A	-	-	-

最小值 典型值 最大值 单位

### 电气特性 $T_J$ = 25 $^{\circ}$ C,除非另有说明。

参数

关断特性							
$B_{VDSS}$	漏极至源极击穿电	$I_D = 250 \mu\text{A},  V_{GS} = 0 \text{V}$	40	-	-	V	
1	<b>是也不适也是由这</b>	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 25 °C	-	-	1	μΑ	
IDSS	漏极至源极漏电流	$V_{GS} = 0 V$ $T_J = 175 ^{\circ}\text{C}  (24)$	-	-	1	mA	
I <sub>GSS</sub>	栅极至源极漏电流	V <sub>GS</sub> = ±20 V	-	-	±100	nA	

测试条件

### 导通特性

符号

$V_{GS(th)}$	栅极至源极阀值电压	$V_{GS} = V_{DS}$	I <sub>D</sub> = 250 μA	2.0	3.2	4.0	V
R <sub>DS(on)</sub>	漏极至源极导通电阻	$I_D = 80 A_{,,}$	T <sub>J</sub> = 25 °C	-	0.90	1.20	mΩ
		V <sub>GS</sub> = 10 V	T <sub>J</sub> = 175 °C (注 4)	-	1.64	1.86	mΩ

### 动态特性

C <sub>iss</sub>	输入电容	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0V, f = 1 MHz		-	7735	-	pF
Coss	输出电容			-	2160	-	pF
C <sub>rss</sub>	反向传输电容			-	129	-	pF
$R_g$	栅极阻抗	f = 1 MHz		-	2.5	-	Ω
$Q_{g(ToT)}$	在 10 V 的栅极总电荷	V <sub>GS</sub> = 0 至 10 V	V <sub>DD</sub> = 32 V	-	90	107	nC
$Q_{g(th)}$	阀值栅极电荷	V <sub>GS</sub> = 0 至 2 V	I <sub>D</sub> = 80 A	-	13.5	15.5	nC
$Q_{gs}$	栅极至源极栅极电荷		_	-	43	-	nC
$Q_{gd}$	栅极至漏极"米勒"电荷			-	10	-	nC

### 开关特性

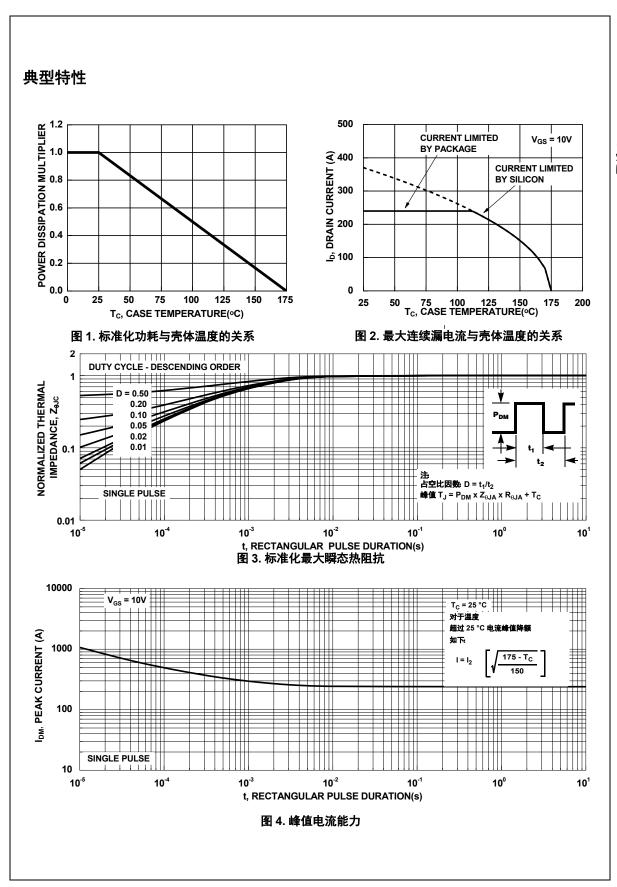
t <sub>on</sub>	导通时间		-	-	102	ns
t <sub>d(on)</sub>	导通延迟		-	33	-	ns
t <sub>r</sub>	上升时间	V <sub>DD</sub> = 20 V, I <sub>D</sub> = 80 A,	-	40	-	ns
t <sub>d(off)</sub>	关断延迟	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	-	47	-	ns
t <sub>f</sub>	下降时间		-	23	-	ns
t <sub>off</sub>	关断时间		-	-	91	ns

### 漏极 - 源极二极管特性

$V_{SD}$	源极至漏极二极管电压	$I_{SD} = 80 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.25	V
		$I_{SD} = 40 \text{ A},  V_{GS} = 0 \text{ V}$	-	-	1.2	V
t <sub>rr</sub>	反向恢复时间	$I_F = 80 \text{ A},  dI_{SD}/dt = 100 \text{ A}/\mu\text{s},$	-	91	107	ns
$Q_{rr}$	反向恢复电荷	V <sub>DD</sub> = 32 V	-	128	167	nC

#### 说明

4: 其最大值根据  $T_J$  = 175 °C 时的设计确定。 在生产中,未对此条件测试产品。



#### 典型特性 I<sub>AS</sub>, AVALANCHE CURRENT (A) 0 2000 若R=0 t<sub>AV</sub>=(L)(l<sub>AS</sub>)/(1.3\* 若R≠0 1000 € **DRAIN CURRENT** 100 100us **OPERATION IN THIS** 10 STARTING T<sub>J</sub> = 25°C AREA MAY BE LIMITED BY rDS(on) 1ms ئ 1 10ms STARTING T<sub>.1</sub> = 150 TJ = MAX RATED 100ms TC = 25°C 0.1 0.001 1000 10000 10 100 0.1 100 200 t<sub>AV</sub>, TIME IN AVALANCHE (ms) 10 V<sub>DS</sub>, DRAIN TO SOURCE VOLTAGE (V) 注:请参考 Fairchild 应用指南 AN7514 和 AN7515 图 5. 正向偏压安全工作区 图 6. 非箝位感性开关性能 400 PULSE DURATION = 80μs Is, REVERSE DRAIN CURRENT (A) DUTY CYCLE = 0.5% MAX V<sub>GS</sub> = 0 V 100 l<sub>D</sub>, DRAIN CURRENT (A) 00 01 081 091 091 T<sub>J</sub> = 175 °C T<sub>J</sub> = 25 °C 10 $T_J = 25^{\circ}C$ $T_{\rm J} = 175^{\rm o}{\rm C}$ $T_J = -55^{\circ}C$ 0 0.1 0.0 0.2 1.2 0.4 0.6 V<sub>GS</sub>, GATE TO SOURCE VOLTAGE (V) $V_{\text{SD}}$ , BODY DIODE FORWARD VOLTAGE (V) 图 7. 传递特性 图 8. 正向二极管特性 300 300 VGS 15V Top DRAIN CURRENT (A) 200 120 100 100 DRAIN CURRENT (A) 250 $V_{GS}$ 10V 8V 7V 15V Top 10V 200 8V 7V 6V 5.5V 5V Bottom 150 5.5V 5V Bottom 80μs PULSE WIDTH 100 Tj=25°C ف ف 50 50 80μs PULSE WIDTH Tj=175°C 0 0 0 V<sub>DS</sub>, DRAIN TO SOURCE VOLTAGE (V) 图 9. 饱和特性 图 10. 饱和特性

### 典型特性

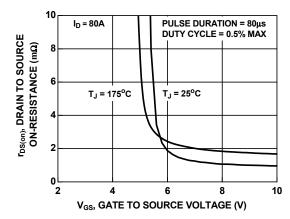


图 11.R<sub>DSON</sub> 与栅极电压的关系

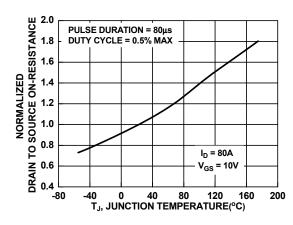


图 12. 标准化 R<sub>DSON</sub> 与结温的关系

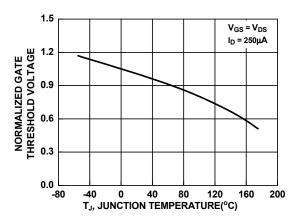


图 13. 标准化栅极阀值电压与温度的关系

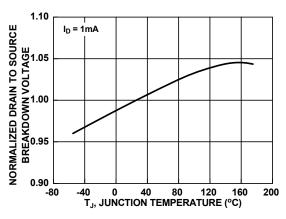


图 14. 标准化漏极至源极击穿电压与结温的关系

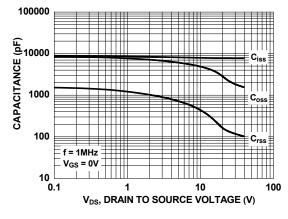


图 15. 电容与漏极一源极电压的关系

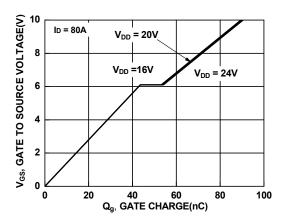
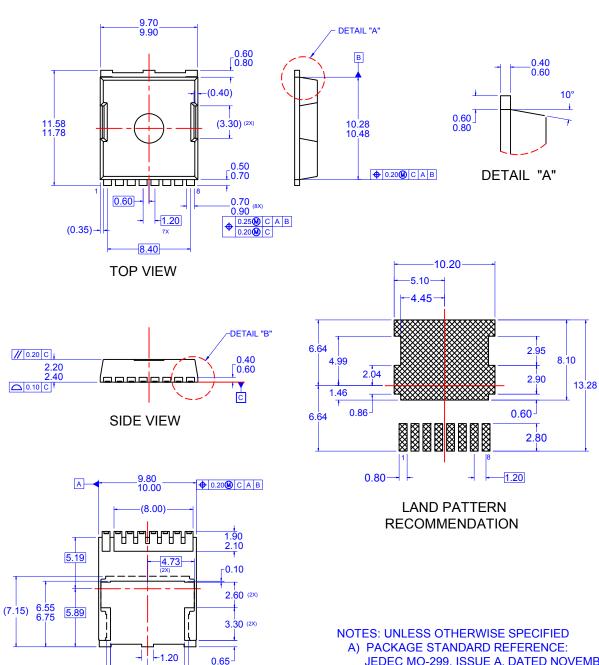


图 16. 栅极电荷与栅极一源极电压的关系



- JEDEC MO-299, ISSUE A, DATED NOVEMBER
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- E) DRAWING FILE NAME: MKT-PSOF08AREV3

-(8.30) **BOTTOM VIEW** 10° - (0.35)

3.75

7.60

0.65-

DETAIL "B"

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